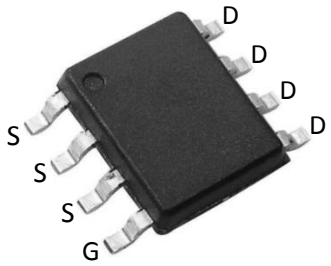
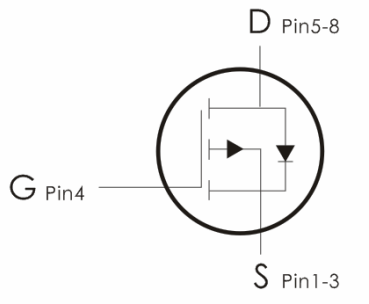
Description：

This P-Channel MOSFET uses advanced trench technology and design to provide excellent $R_{DS(on)}$ with low gate charge.

It can be used in a wide variety of applications.





Features：

1) V_{DS}=-60V,I_D=-5A,$R_{DS(ON)}$<95mΩ @V_{GS}=-10V
2) Low gate charge.
3) Green device available.
4) Advanced high cell denity trench technology for ultra low $R_{DS(ON)}$.
5) Excellent package for good heat dissipation.

Absolute Maximum Ratings： (T_C=25℃ unless otherwise noted)

Symbol	Parameter	Ratings	Units
V_{DS}	Drain-Source Voltage	-60	V
V_{GS}	Gate-Source Voltage	±20	V
I_D	Continuous Drain Current-T_A=25℃	-5	A
	Continuous Drain Current-T_A=70℃	-3.2	
I_{DM}	Pulsed Drain Current[2]	-8.2	A
E_{AS}	Single Pulse Avalanche Energy[3]	29.7	mJ
I_{AS}	Avalanche Current	24.4	A
P_D	Power Dissipation[4]	3.1	W
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to +150	℃

Thermal Characteristics：

Symbol	Parameter	Max	Units
$R_{\theta JA}$	Thermal Resistance,Junction to Ambient[1]	85	℃/ W

$R_{\theta JC}$	Thermal Resistance Junction-Case[1]	36	℃/ W

Electrical Characteristics： (T_J=25℃ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain-Sourtce Breakdown Voltage	V_{GS}=0V,I_D=250μA	-60	---	---	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{GS}=0V, V_{DS}=-48V, TJ=25℃	---	---	1	μA
		V_{GS}=0V, V_{DS}=-48V, TJ=55℃	---	---	5	μA
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±20V, V_{DS}=0A	---	---	±100	nA
On Characteristics						
$V_{GS(th)}$	GATE-Source Threshold Voltage	V_{GS}=V_{DS}, I_D=250μA	-1.2	---	-2.5	V
$R_{DS(ON)}$	Drain-Source On Resistance[2]	V_{GS}=-10V,I_D=-3A	---	75	95	mΩ
		V_{GS}=-4.5V,I_D=-2A	---	95	130	
G_{FS}	Forward Transconductance	V_{DS}=-5V, I_D=-3A	---	8.7	---	S
R_G	Gate Resistance	V_{DS}=0V , V_{GS}=0V , f=1MHz	---	15	---	Ω
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS}=-15V, V_{GS}=0V, f=1MHz	---	980	---	pF
C_{oss}	Output Capacitance		---	65	---	
C_{rss}	Reverse Transfer Capacitance		---	48	---	
Switching Characteristics[3]						
$t_{d(on)}$	Turn-On Delay Time	V_{DD}=-15V, V_{GS}=-10V I_D=-1A,R_G=3.3Ω	---	8.8	---	ns
t_r	Rise Time		---	19.6	---	ns
$t_{d(off)}$	Turn-Off Delay Time		---	47.2	---	ns
t_f	Fall Time		---	9.6	---	ns

Q_g	Total Gate Charge	V_{DS}=-48V , V_{GS}=-4.5V , I_D=-3A	---	11.8	---	nC
Q_{gs}	Gate-Source Charge		---	1.9	---	nC
Q_{gd}	Gate-Drain Charge		---	6.5	---	nC
Drain-Source Diode Characteristics						
V_{SD}	Source-Drain Diode Forward Voltage[2]	V_{GS}=0V,I_S=-1A, T_J=25℃	---	---	-1.2	V
I_S	Continuous Source Current[1,5]	V_G=V_D=0V , Force Current	---	---	-4.1	A
I_{SM}	Pulsed Source Current[2,5]		---	---	-8.2	A

Notes:

1.The data tested by surface mounted on a 1 inch FR-4 board with 2OZ copper.
2.The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%
3.The EAS data shows Max. rating . The test condition is V_{DD}=-25V,V_{GS}=-10V,L=0.1mH,I_{AS}=-24.4A
4.The power dissipation is limited by 150℃ junction temperature
5.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

Typical Characteristics: (T_C=25℃ unless otherwise noted)

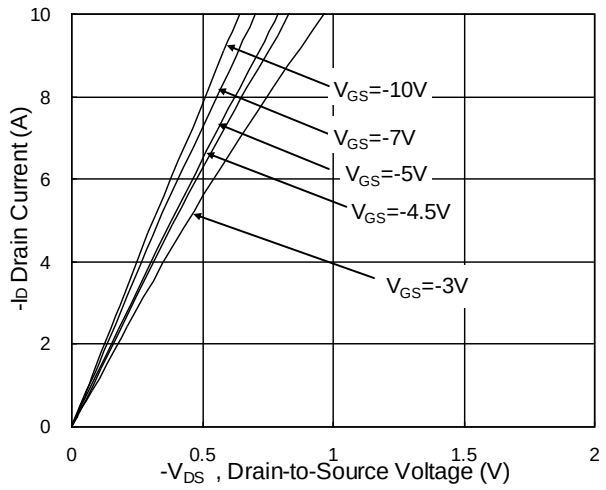


Fig.1 Typical Output Characteristics

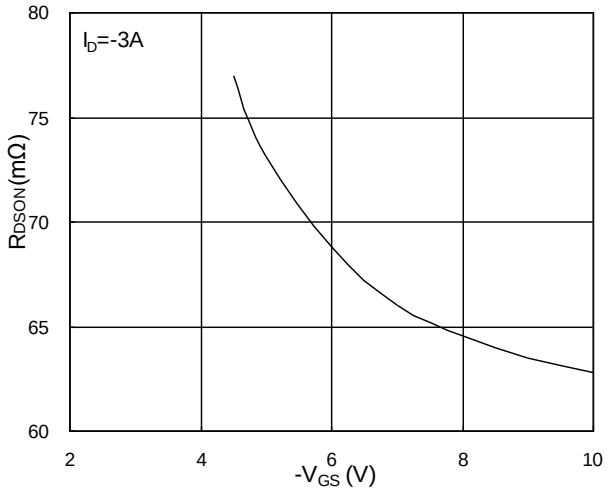


Fig.2 On-Resistance v.s Gate-Source

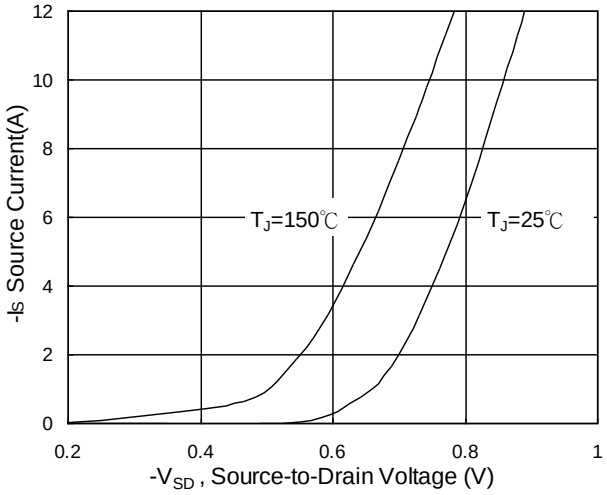


Fig.3 Forward Characteristics of Reverse

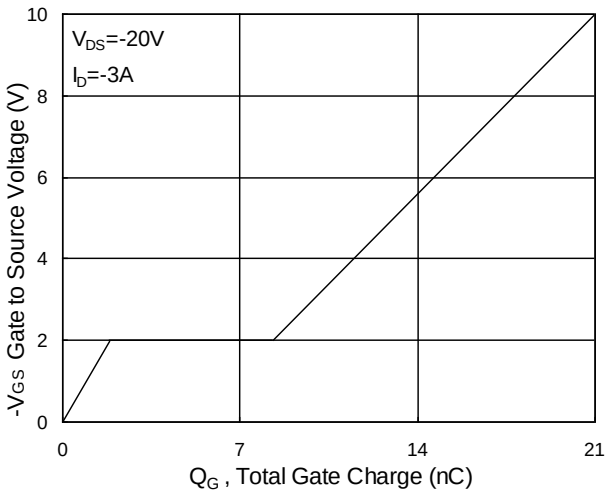


Fig.4 Gate-Charge Characteristics

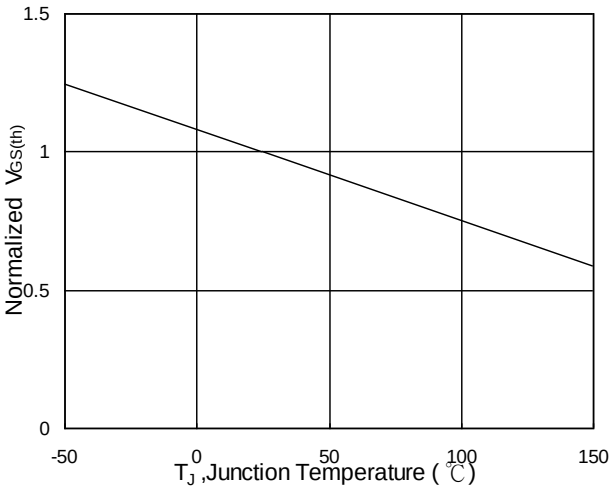


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

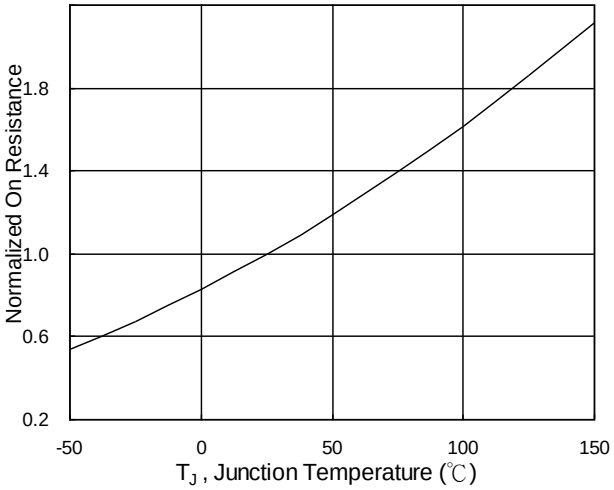


Fig.6 Normalized R_{DSON} vs. T_J

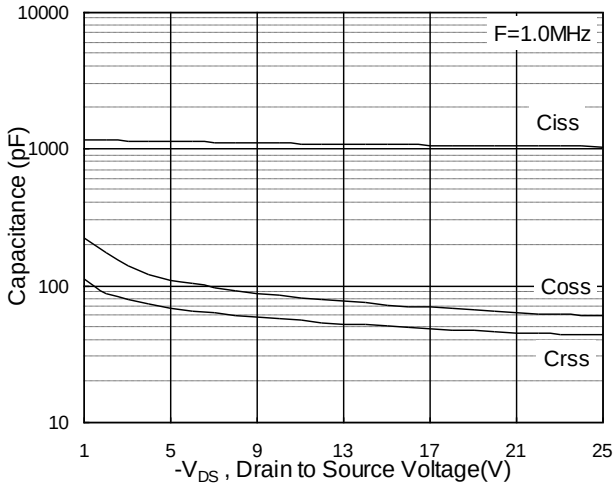


Fig.7 Capacitance

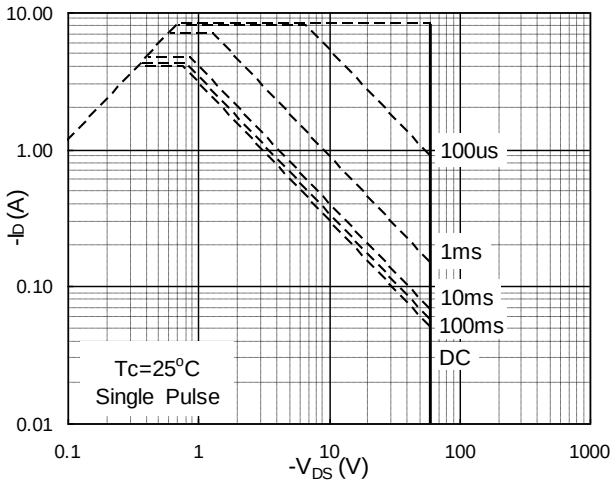


Fig 8 Safe Operating Area

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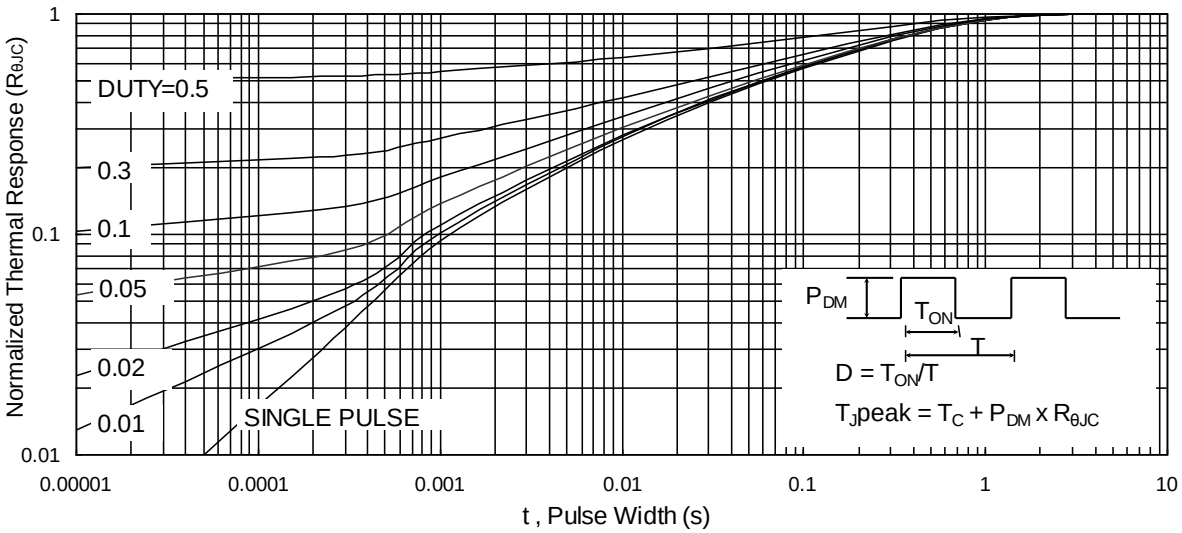

Fig.9 Normalized Maximum Transient Thermal Impedance

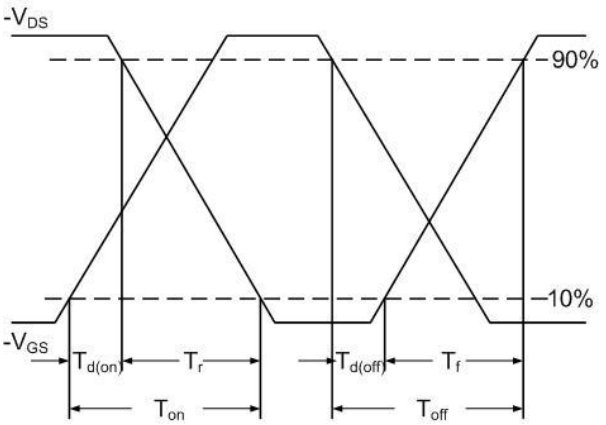

Fig.10 Switching Time Waveform

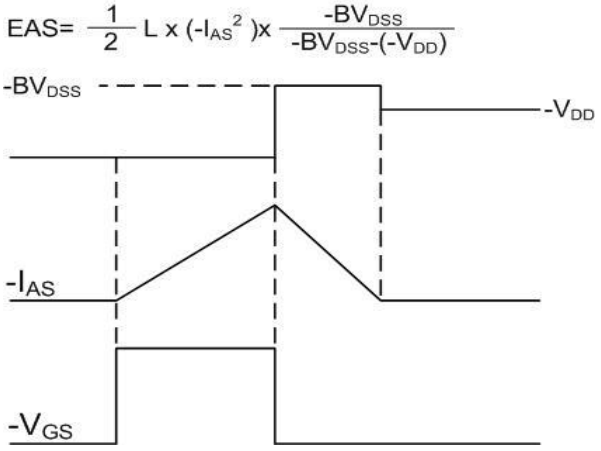

Fig.11 Unclamped Inductive Waveform